

October 2008

FJP3305

High Voltage Fast-Switching NPN Power Transistor

- · High Voltage Capability
- · High Switching Speed
- · Suitable for Electronic Ballast and Switching Regulator



1.Base 2.Collector 3.Emitter

Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	700	V
V _{CEO}	Collector-Emitter Voltage	400	V
V _{EBO}	Emitter-Base Voltage	9	V
I _C	Collector Current (DC)	4	A
I _{CP}	Collector Current (Pulse)	8	A
I _B	Base Current	2	A
P _C	Collector Dissipation (T _C = 25°C)	75	W
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature	-65 ~ 150	°C

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Conditions	Min.	Тур.	Max	Units
BV _{CBO}	Collector-Base Breakdwon Voltage	I _C = 500μA, I _E = 0	700			V
BV _{CEO}	Collector-Emitter Breakdown Voltage	$I_{C} = 5mA, I_{B} = 0$	400			V
BV _{EBO}	Emitter-Base Breakdown Voltage	$I_E = 500 \mu A, I_C = 0$	9			V
I _{CBO}	Collector Cut-off Current	V _{CB} = 700V, I _E = 0			1	μА
I _{EBO}	Emitter Cut-off Current	$V_{EB} = 9V, I_{C} = 0$			1	μА
h _{FE1} h _{FE2}	DC Current Gain *	V _{CE} = 5V, I _C = 1A V _{CE} = 5V, I _C = 2A	19 8		35 40	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_C = 1A, I_B = 0.2A$ $I_C = 2A, I_B = 0.5A$ $I_C = 4A, I_B = 1A$			0.5 0.6 1.0	V V V
V _{BE(sat)}	Base-Emitter Saturation Voltage	$I_C = 1A, I_B = 0.2A$ $I_C = 2A, I_B = 0.5A$			1.2 1.6	V V
f _T	Current Gain Bandwidth Product	$V_{CE} = 10V, I_{C} = 0.5A$	4			MHz
C _{ob}	Output Capacitance	V _{CB} = 10V, f = 1MHz		65		pF
t _{ON}	Turn On Time	V _{CC} = 125V, I _C = 2A			0.8	μS
t _{STG}	Storge Time	$I_{B1} = -I_{B2} = 0.4A$ $R_1 = 62.5\Omega$			4.0	μS
t _F	Fall Time	11/2 - 02.052			0.9	μS

^{*} Pulse Test: PW $\leq 300 \mu s, \, \text{Duty Cycle} \leq 2\%$

h_{FE} Classification

Classification	H1	H2
h _{FE1}	19 ~ 28	26 ~ 35

Typical Performance Characteristics

Figure 1. Static Characteristic

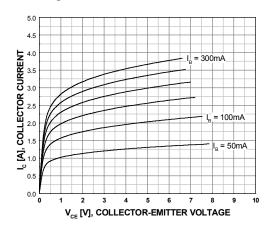


Figure 3. DC Current Gain (O-Grade)

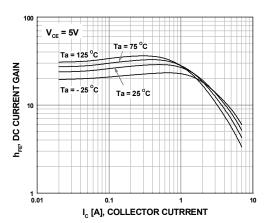


Figure 5. Saturatin Voltage (O-Grade)

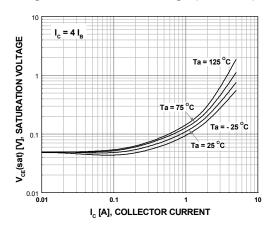


Figure 2. DC Current Gain (R-Grade)

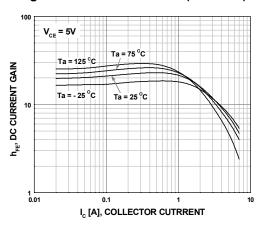


Figure 4. Saturation Voltage (R-Grade)

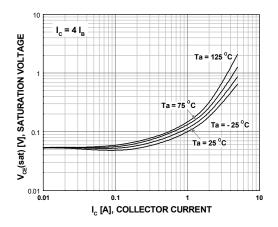
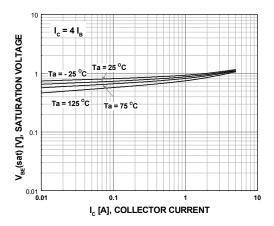


Figure 6. Saturation Voltage (R-Grade)



Typical Performance Characteristics (Continued)

Figure 7. Saturation Voltage (O-Grade)

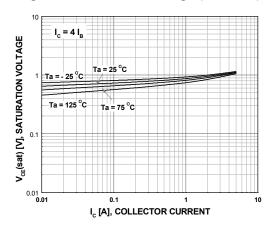


Figure 8. Switching Time

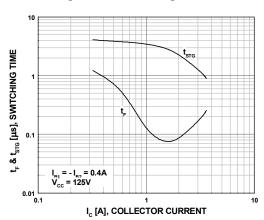
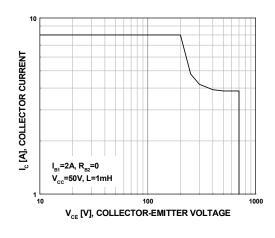


Figure 9. Reverse Biased Safe Operating Area

Figure 10. Forward Biased Safe Operating Area



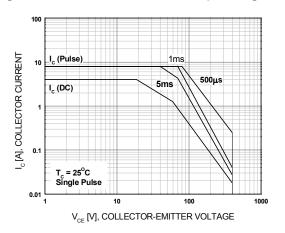
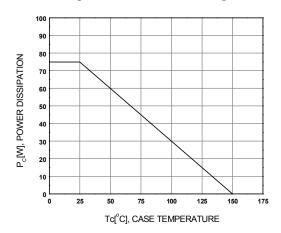


Figure 11. Power Derating





ON Semiconductor and in are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdt/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor and see any inability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and ex

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800-282-9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative